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(19)

(11) Publication number:

08264530

Generated Document.

PATENT ABSTRACTS OF JAPAN(21) Application number: **07061278**

(51) Intl. Cl.: **H01L 21/3205 C23C 16/14 C23F 4/00**
C30B 25/06 H01L 21/28 H01L 21/285
H01L 21/3065

(22) Application date: **20.03.95**

(30) Priority:

(43) Date of application
 publication: **11.10.96**

(84) Designated contracting
 states:

(71) Applicant: **FUJITSU LTD**

(72) Inventor: **NISHIBE HARUHITO**
IIO KOKI

(74) Representative:

(54) METHOD AND SYSTEM
FOR FABRICATING
SEMICONDUCTOR DEVICE

(57) Abstract:

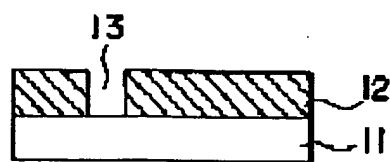
PURPOSE: To realize continuous deposition in a same chamber by forming a first tungsten film on an insulation layer through reduction of diborane and then forming a second tungsten film thereon through reduction of hydrogen or silane.

CONSTITUTION: A mixture gas of WF₆ gas, B₂H₆ gas and H₂ gas is fed into a chamber and a first tungsten film 14 is formed on an insulation layer 12 by CVD. In this regard, the WF₆ gas is principally reduced by the B₂H₆ gas thus forming an adhesion layer 14. Subsequently, supply of the B₂H₆ gas is stopped and the mixture gas of WF₆ gas and H₂ gas is fed into a chamber and a conductive layer 15 of second tungsten is formed by CVD. In this regard, the WF₆ gas is

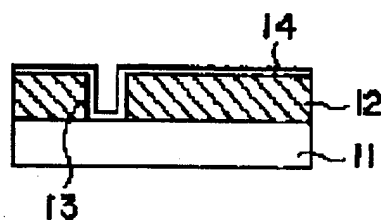
reduced by the H₂ gas thus forming the layer 15. Since the deposition can be carried out continuously in same chamber by simply switching the reaction gas, throughput can be enhanced.

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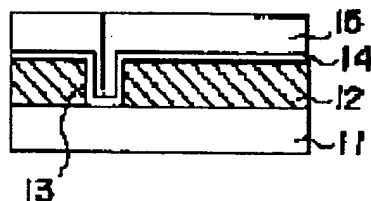
(a)



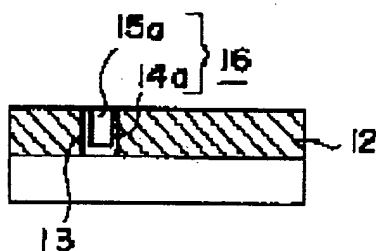
(b)



(c)



(d)



(e)

